In the Claims:

Claim 13 is amended herein. The remaining claims are not amended in this response.

1. (original) A receiver comprising:

a high frequency receiving circuit for which a reception frequency in accordance with a tuning voltage is set;

a local oscillator for generating a local oscillation signal of a frequency in accordance with a control voltage;

a mixing circuit for mixing a signal outputted from said high frequency receiving circuit with said local oscillation signal;

a setting data generating unit for outputting setting data corresponding to a predetermined reception frequency; and

a digital-analog converter for generating said tuning voltage corresponding to the setting data outputted from said setting data generating unit, the tuning voltage being changed with a predetermined temperature coefficient in accordance with ambient temperature.

2. (original) The receiver according to claim 1, wherein said high frequency receiving circuit and said local oscillator, each includes a resonance circuit in which a variable capacitance diode of which electrostatic capacitance can be changed by said

control voltage or said tuning voltage, is connected with a coil, and

wherein in each of said resonance circuits, said variable capacitance diode and said coil are connected in a same form.

3. (original) The receiver according to claim 1, wherein said digital-analog converter changes said tuning voltage in accordance with ambient temperature so as to prevent the reception frequency of said high frequency receiving circuit from fluctuating in accordance with variation of ambient temperature.

4. (original) The receiver according to claim 1, wherein said digital-analog converter comprises a temperature coefficient setting section constituted by including elements having predetermined temperature coefficients, and

wherein a device constant of said temperature coefficient setting section as a whole is changed in accordance with ambient temperature.

5. (original) The receiver according to claim 4, wherein said temperature coefficient setting section includes a plurality of resistances which is formed by a semiconductor manufacturing process and which have temperature coefficients different to each other, and

wherein a connection form of said plurality of resistances is set so that a temperature coefficient of said digital-analog converter becomes a predetermined value.

6. (original) The receiver according to claim 5, wherein each of said plurality of resistances is formed by a poly-silicon on a semiconductor substrate, and wherein the temperature coefficients are made different by adjusting impurity concentration and carrier types of said poly-silicon.

7. (original) The receiver according to claim 5, wherein each of said plurality of resistances is formed by utilizing a p-type region or an n-type region on a semiconductor substrate, and wherein the temperature coefficients are made different by adjusting impurity concentration and carrier types of said p-type region or said n-type region.

8. (original) The receiver according to claim 4, wherein said digital-analog converter comprises a current source of which current value is set in accordance with a value of said inputted setting data, and said temperature coefficient setting section into which a current generated by the current source flows, and wherein said digital-analog converter outputs a voltage across said temperature coefficient setting section as said tuning voltage.

9. (original) A digital-analog converter comprising a temperature coefficient setting section constituted by including elements having predetermined temperature coefficients,

wherein an output voltage corresponding to input data is changed with a predetermined temperature coefficient in

accordance with ambient temperature, by changing a device constant of said temperature coefficient setting section as a whole in accordance with ambient temperature.

10. (original) The digital-analog converter according to claim 9, wherein said temperature coefficient setting section comprises a plurality of resistances which is formed by a semiconductor manufacturing process and which have temperature coefficients different to each other, and

wherein a connection form of said plurality of resistances is set so that a temperature coefficient of said plurality of resistances as a whole becomes a predetermined value.

11. (original) The digital-analog converter according to claim 10, wherein each of said plurality of resistances is formed by a poly-silicon on a semiconductor substrate, and wherein the temperature coefficient is made different by adjusting impurity concentration and carrier types of said poly-silicon.

12. (original) The digital-analog converter according to claim 10, wherein each of said plurality of resistances is formed by utilizing a p-type region or an n-type region on a semiconductor substrate, and wherein the temperature coefficient is made different by adjusting impurity concentration and carrier types of said p-type region or said n-type region.

13. (currently amended) The digital-analog converter according to claim 9, further comprising a current source of which current value is set in accordance with a value of ~~said~~ an inputted setting data,

wherein a current generated by said current source flows into said temperature coefficient setting section and a voltage across said temperature coefficient setting section is outputted as said tuning voltage.

14. (original) A tuning circuit having a tuning frequency being set in accordance with a tuning voltage generated by using the digital-analog converter according to claim 9,

said tuning circuit making said tuning frequency kept constant by changing said tuning voltage generated by said digital-analog converter in accordance with said temperature coefficient, when ambient temperature is changed.